

MA735

Silicon epitaxial planer type

For high-frequency rectification

■ Features

- Forward current (average) $I_{F(AV)}$: 1A type
- Reverse voltage (DC value) V_R : 30V
- Automatic insertion possible with emboss taping

■ Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	30	V
Repetitive peak reverse voltage	V_{RRM}	30	V
Average forward current	$I_{F(AV)}^{*1}$	1	A
Non-repetitive peak forward surge current	I_{FSM}^{*2}	30	A
Junction temperature	T_j	- 40 to +125	$^\circ\text{C}$
Storage temperature	T_{stg}	- 40 to +125	$^\circ\text{C}$

* 1 With a printed-circuit board (copper foil area $2\text{mm} \times 2\text{mm}$ or more on both cathode and anode sides)

* 2 50Hz sine wave, one-cycle wave, high value (non-repetitive)

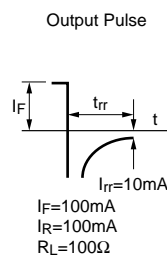
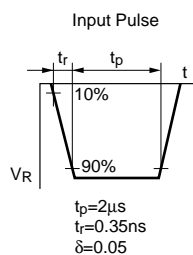
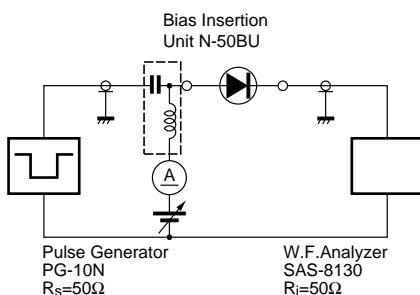
■ Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Condition	min	typ	max	Unit
Reverse current (DC)	I_R	$V_R = 30\text{V}$			1	mA
Forward voltage (DC)	V_F	$I_F = 1\text{A}$			0.5	V
Terminal capacitance	C_t	$V_R = 10\text{V}$, $f = 1\text{MHz}$		50		pF
Reverse recovery time	t_{rr}^*	$I_F = I_R = 100\text{mA}$ $I_{rr} = 10\text{mA}$, $R_L = 100\Omega$			30	ns

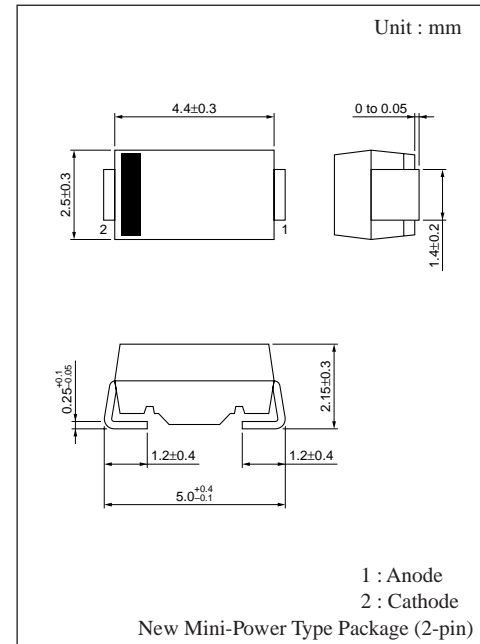
Note 1. Schottky barrier diode is sensitive to electric shock (static electricity, etc.). Due attention must be paid on charge of a human body and leakage from the equipment used.

2. Rated input/output frequency : 20MHz

3. * t_{rr} measuring circuit

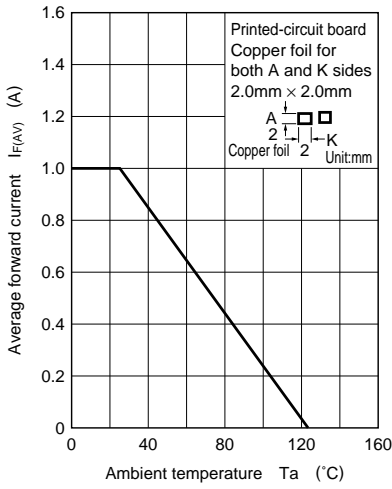


■ Marking

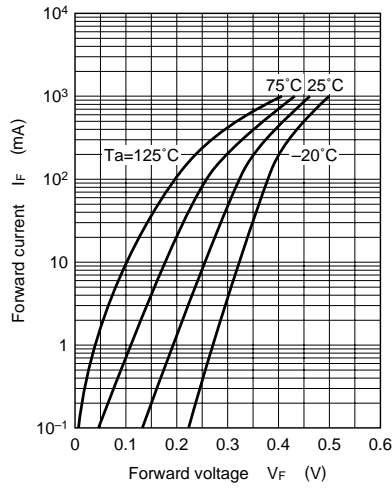


Marking Symbol : PA

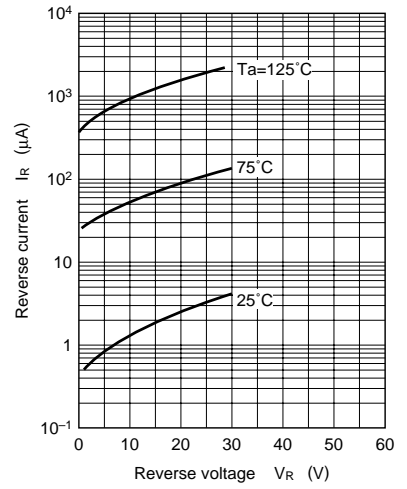
$I_{F(AV)} - T_a$



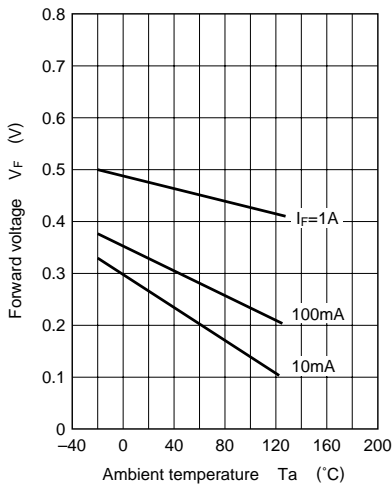
$I_F - V_F$



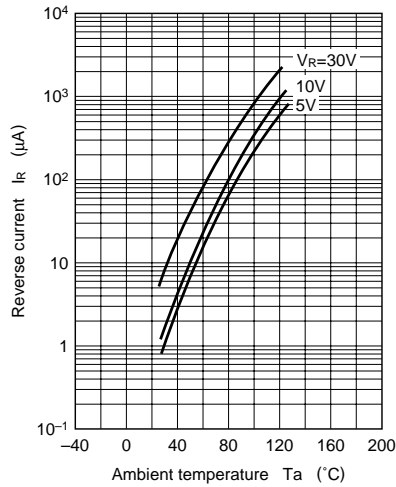
$I_R - V_R$



$V_F - T_a$



$I_R - T_a$



$C_t - V_R$

